

NPN Darlington transistor

BSR52

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

APPLICATIONS

- Industrial high gain amplification.

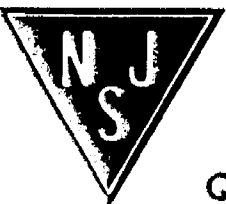
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	90	V
V_{CES}	collector-emitter voltage	$V_{BE} = 0$ V	–	80	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	1	A
I_{CM}	peak collector current		–	2	A
I_B	base current (DC)		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	830	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.



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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	150	K/W

Note

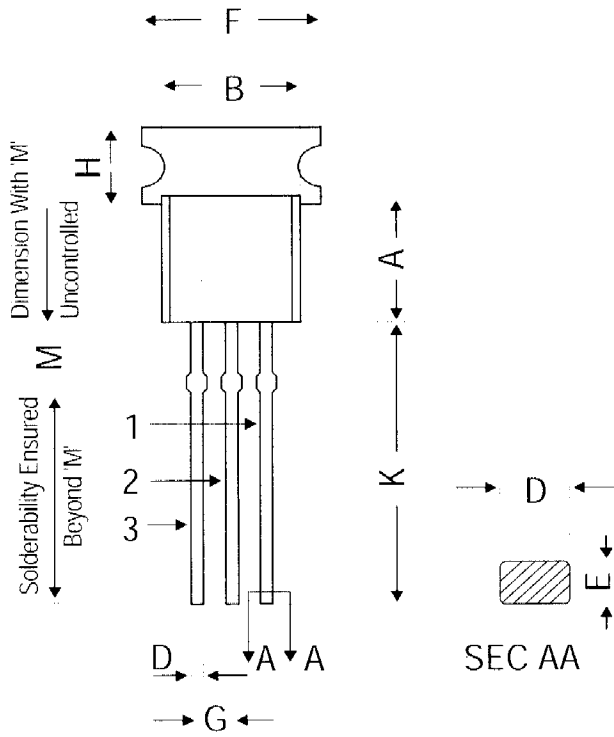
1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

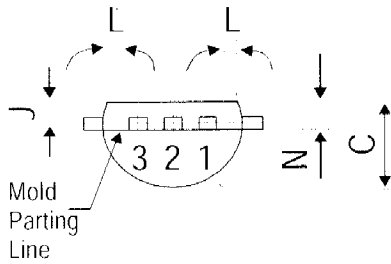
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	collector-base cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = 80\text{ V}$	–	–	50	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\text{ V}; I_C = 0\text{ A}$	–	–	50	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}$; see Fig.2 $I_C = 150\text{ mA}$ $I_C = 500\text{ mA}$	1000 2000	– –	– –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 0.5\text{ mA}$	–	–	1.3	V
		$I_C = 1\text{ A}; I_B = 4\text{ mA}$	–	–	1.6	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 0.5\text{ mA}$	–	–	1.9	V
		$I_C = 1\text{ A}; I_B = 4\text{ mA}$	–	–	2.2	V
f_T	transition frequency	$V_{CE} = 5\text{ V}; I_C = 500\text{ mA};$ $f = 100\text{ MHz}$	–	200	–	MHz
Switching times (between 10% and 90% levels); see Fig.3						
t_{on}	turn-on time	$I_{Con} = 500\text{ mA}; I_{Bon} = 0.5\text{ mA};$	–	–	500	ns
t_{off}	turn-off time	$I_{Boff} = -0.5\text{ mA}$	–	–	1300	ns

TO-237 Plastic Package



DIM	MIN.	MAX.
A	4.32	5.33
B	4.45	5.20
C	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	—	5.40
G	1.14	1.40
H	—	2.54
J	1.03	1.20
K	12.70	—
L	5 DEG	
M	1.982	2.082
N	1.20	1.40

All dimensions are in mm



PIN CONFIGURATION

1. COLLECTOR
2. BASE
3. EMITTER

